

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of Chang Gyu KIM et al. ) METHOD FOR FORMING ISOLATION  
Korean Application No. 2001-15415        ) LAYER OF SEMICONDUCTOR DEVICE  
    )  
Korean Filing Date: March 24, 2001      )  
    )  
    )

**PRELIMINARY AMENDMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Please amend the subject application as follows:

**In the Specification**

**--CROSS REFERENCE TO RELATED APPLICATION**

This application claims the priority of Korean patent application Serial No. 2001-15415  
filed on March 24, 2001.-

**In the Abstract**

Please replace the abstract presently on file with the new abstract presented herewith.

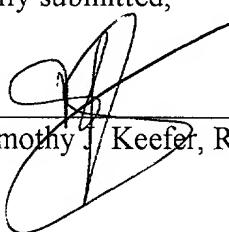
**ABSTRACT OF THE DISCLOSURE**

[A method for forming an isolation layer of a semiconductor device is disclosed. The method has a wet etching separately performed two times or more without a conventional chemical mechanical polishing process. In the] A method in which, a silicon substrate in which an active region and a field region are defined is provided, and a trench is formed in the silicon

substrate within the field region. An insulating layer to be used as the isolation layer is then formed on the silicon substrate including the trench. Thus the trench is filled with the insulating layer. Next, a capping layer is formed on a resultant entire structure including the insulating layer, and selectively removed to expose an upper portion of the insulating layer in the active region. The exposed insulating layer in the active region is then removed by a first wet etching, and the residual capping layer is removed by a second wet etching. Accordingly, the isolation layer is obtained from the insulating layer remaining in the trench.

Respectfully submitted,

Date: 11/14/01  
WILDMAN, HARROLD, ALLEN & DIXON  
225 West Wacker Drive  
Chicago, IL 60606  
Ph. 312/201-2000  
Fax 312/201-2555

By:   
Timothy J. Keefer, Reg. No. 35567

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I hereby certify that this paper or file is being deposited with the United States Postal Service Express Mail<sup>®</sup> service. Addressee to the date indicated above and is addressed to the Assistant Commissioner for Patents Washington, D.C. 20231.  
Melissa Parada

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**CLEAN VERSION OF ABSTRACT**

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